

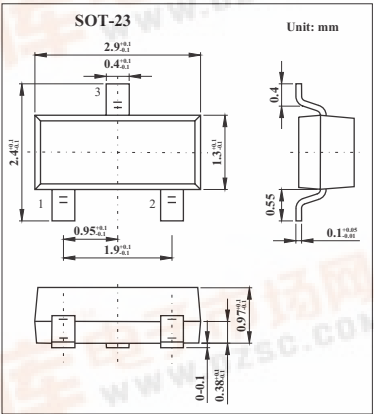
SMD Type

Diodes

Silicon Schottky Barrier Diode
HRW0502A

■ Features

- Low forward voltage drop and suitable for high efficiency rectifying.
- MPAK package is suitable for high density surface mounting and high speed assembly.



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	VRRM	20	V
Average rectified current	Io	500	mA
Non-repetitive peak forward surge current	IFSM (Note 1)	5	A
Junction temperature	Tj	125	℃
Storage temperature	Tstg	-55 to + 125	℃

Note

1. 10msec sine wave 1 pulse

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	VF	IF = 500 mA			0.40	V
Reverse current	IR	VR = 20 V			200	μ A
Capacitance	C	VR = 0 V, f = 1MHz		120		pF
Thermal resistance	Rth(j-a)	Polyimide board		340		℃/W

■ Marking

Marking	S10
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